

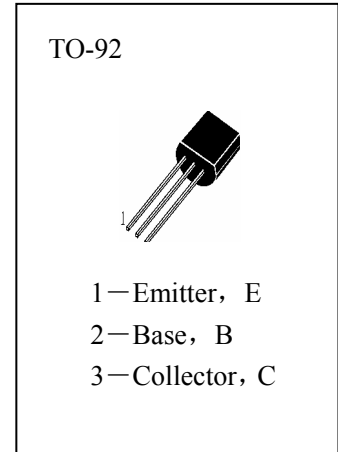


H1008

■ Low Frequency Amplifier Medium Speed Switching

■ ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

T _{stg}	Storage Temperature	-55~150°C
T _j	Junction Temperature	150°C
P _C	Collector Dissipation	800mW
V _{CBO}	Collector-Base Voltage	80V
V _{CEO}	Collector-Emitter Voltage	60V
V _{EBO}	Emitter-Base Voltage	8V
I _C	Collector Current	700mA



■ ELECTRICAL CHARACTERISTICS (T_a=25°C)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
I _{CBO}	Collector Cut-off Current			100	nA	V _{CB} =60V, I _E =0
I _{EBO}	Emitter Cut-off Current			100	nA	V _{EB} =5V, I _C =0
H _{FE(1)}	DC Current Gain	40		400		V _{CE} =2V, I _C =50mA
V _{CE(sat)}	Collector- Emitter Saturation Voltage		0.2	0.4	V	I _C =500mA, I _B =50mA
V _{BE(sat)}	Base-Emitter Saturation Voltage		0.86	1.1	V	I _C =500mA, I _B =50mA
BV _{CBO}	Collector-Base Breakdown Voltage	80			V	I _C =100 μ A, I _E =0
BV _{CEO}	Collector-Emitter Breakdown Voltage	60			V	I _C =10mA, I _B =0
BV _{EBO}	Emitter-Base Breakdown Voltage	8			V	I _E =10 μ A, I _C =0
f _T	Current Gain-Bandwidth Product	30	50		MHz	V _{CE} =10V, I _C =50mA
C _{ob}	Output Capacitance		8		pF	V _{CB} =10V, I _E =0, f=1MHz

■ h_{FE} Classification

R	O	Y	GR
40—80	70—140	120—240	240—400

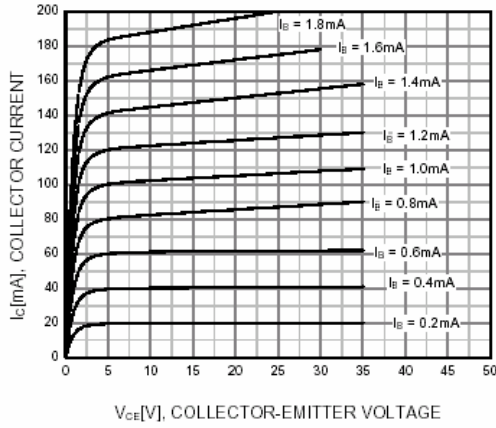
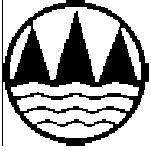


Figure 1. Static Characteristic

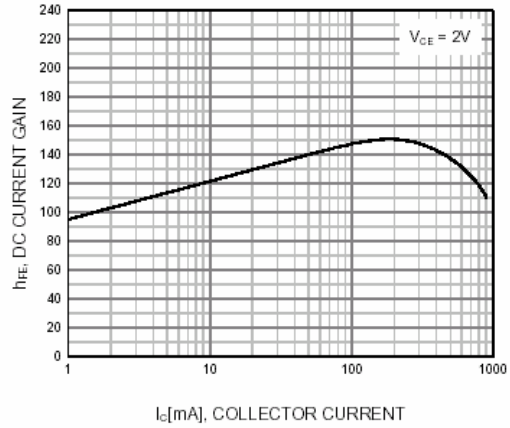


Figure 2. DC current Gain

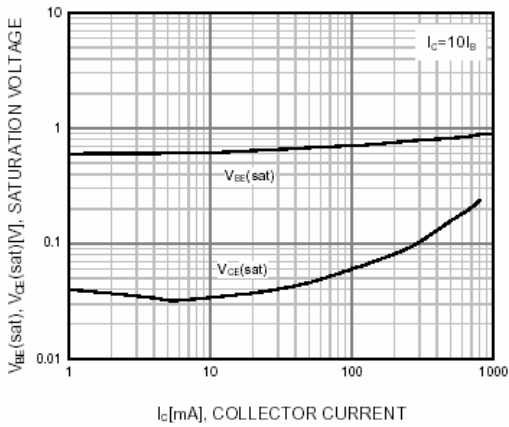


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

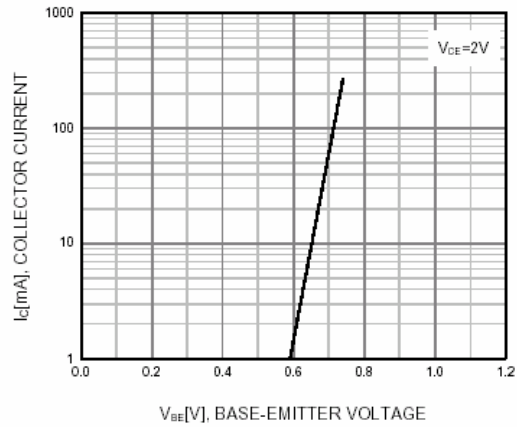


Figure 4. Base-Emitter On Voltage

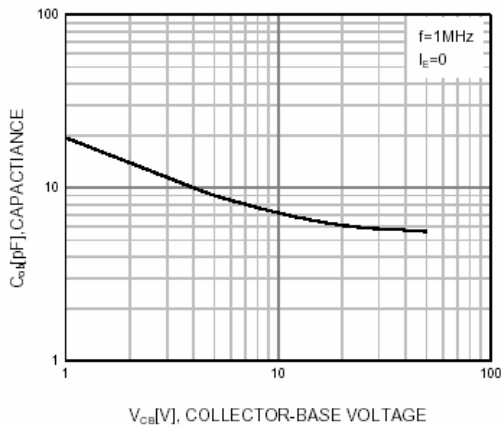


Figure 5. Collector Output Capacitance